

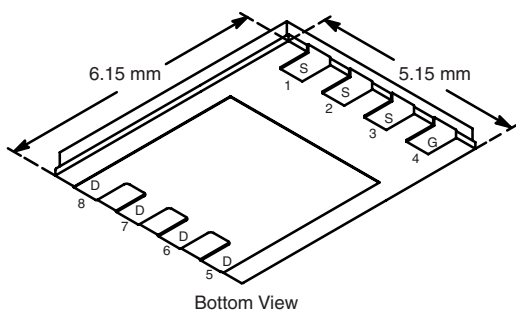


P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) | Q_g (Typ.) |
|--------------|-----------------------------|-------------------|--------------|
| - 30 | 0.007 at $V_{GS} = -10$ V | - 30 ^d | 63 nC |
| | 0.0105 at $V_{GS} = -4.5$ V | - 30 ^d | |

PowerPAK SO-8



Bottom View

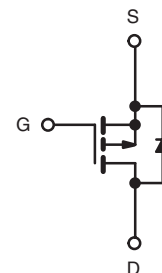
FEATURES

- Halogen-free
- TrenchFET® Power MOSFET
- 100% R_g Tested
- 100% UIS Tested

RoHS
COMPLIANT

APPLICATIONS

- Notebook Battery Charging
- Notebook Adapter Switch
- Load Switch



Ordering Information: Si7159DP-T1-GE3 (Lead (Pb)-free and Halogen-free)

P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

| Parameter | Symbol | Limit | Unit |
|--|----------------|---------------|------|
| Drain-Source Voltage | V_{DS} | - 30 | V |
| Gate-Source Voltage | V_{GS} | ± 25 | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_C = 25$ °C | A |
| | | $T_C = 70$ °C | |
| | | $T_A = 25$ °C | |
| | | $T_A = 70$ °C | |
| Pulsed Drain Current | I_{DM} | - 60 | A |
| Continuous Source-Drain Diode Current | I_S | $T_C = 25$ °C | |
| | | $T_A = 25$ °C | |
| Avalanche Current | I_{AS} | - 20 | |
| Single-Pulse Avalanche Energy | E_{AS} | 20 | mJ |
| Maximum Power Dissipation | P_D | $T_C = 25$ °C | W |
| | | $T_C = 70$ °C | |
| | | $T_A = 25$ °C | |
| | | $T_A = 70$ °C | |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |
| Soldering Recommendations (Peak Temperature) ^{e, f} | | 260 | |

THERMAL RESISTANCE RATINGS

| Parameter | Symbol | Typical | Maximum | Unit |
|---|------------|---------|---------|------|
| Maximum Junction-to-Ambient ^{a, c} | R_{thJA} | 18 | 33 | °C/W |
| Maximum Junction-to-Case | R_{thJC} | 1.0 | 1.5 | |

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. $t = 10$ s.

c. Maximum under Steady State conditions is 65 °C/W.

d. Package limited.

e. See Solder Profile (<http://www.vishay.com/doc?73257>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

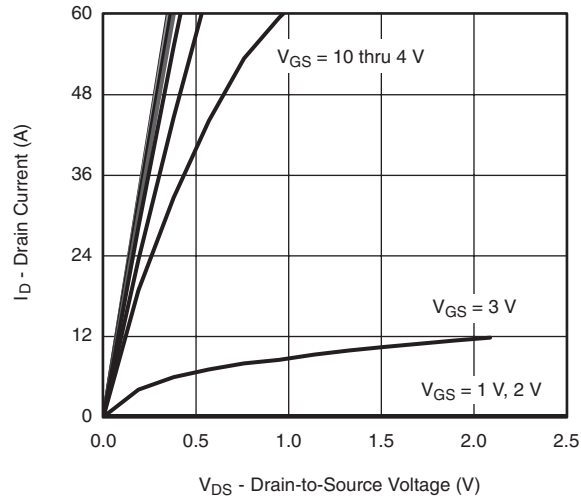
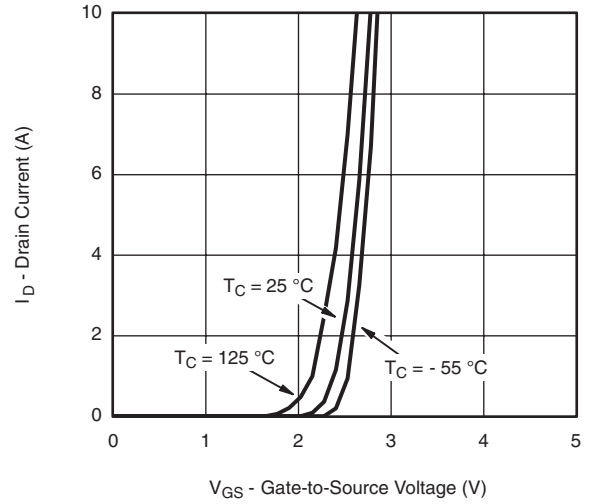
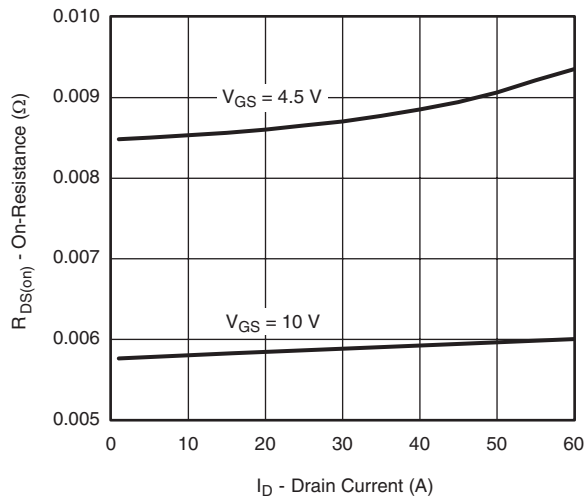
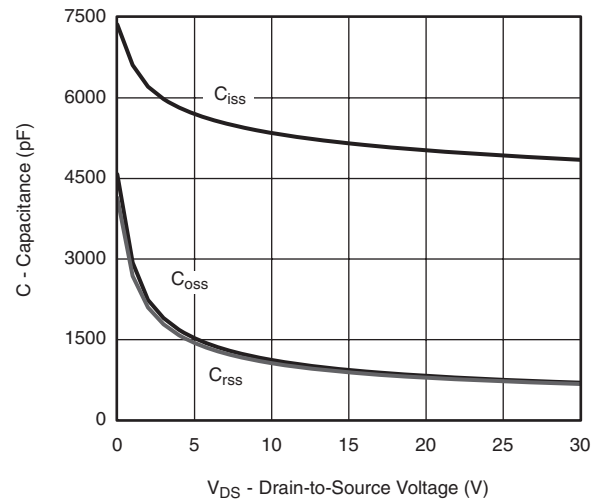
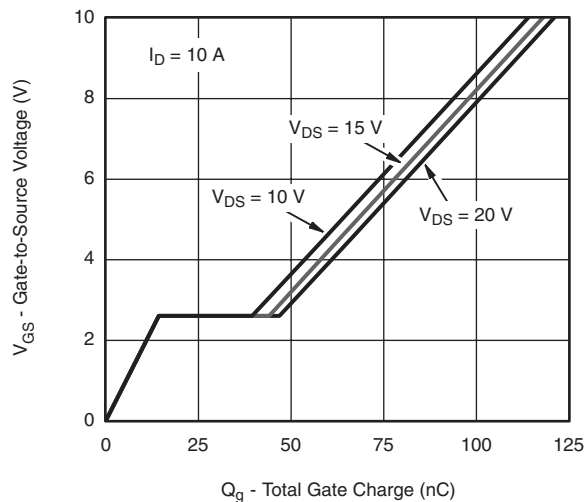
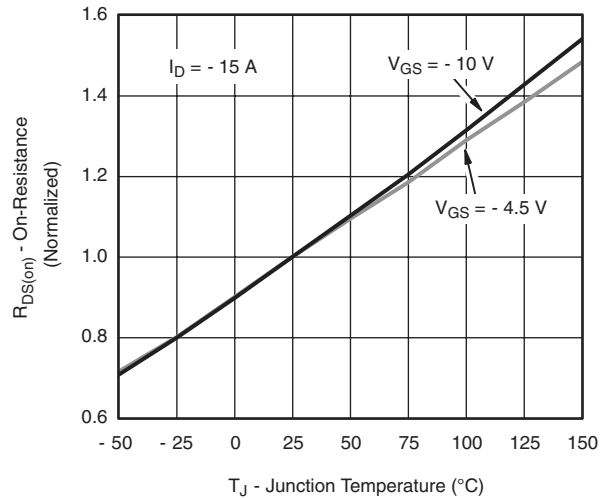
f. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

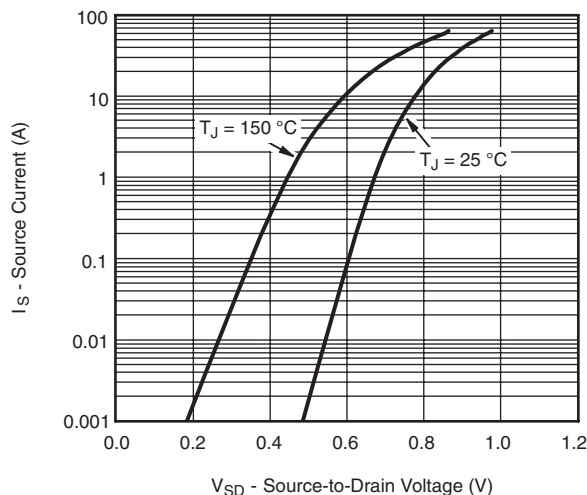
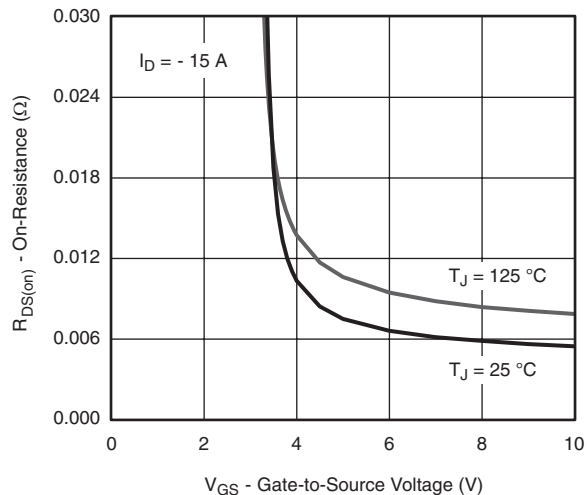
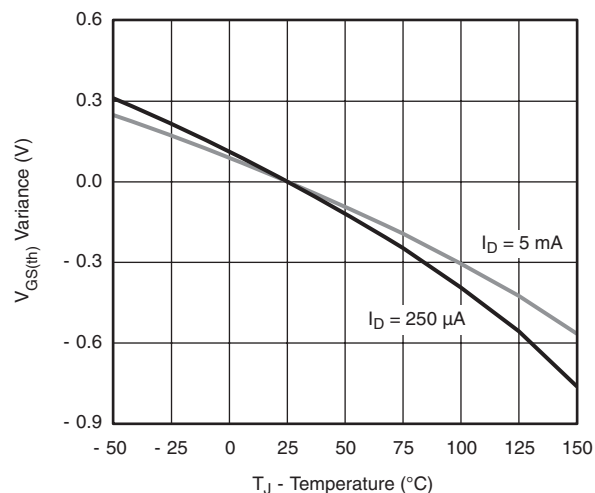
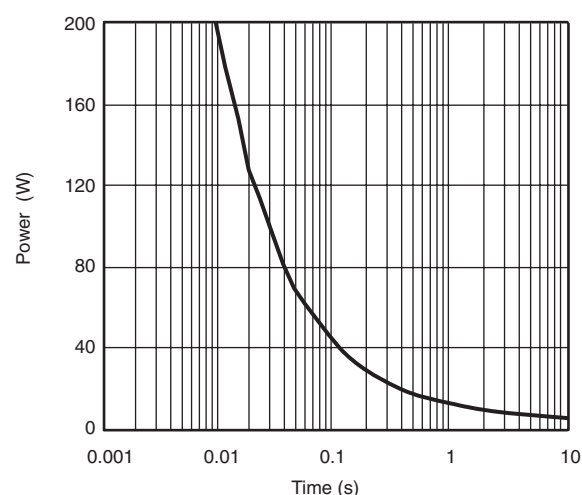
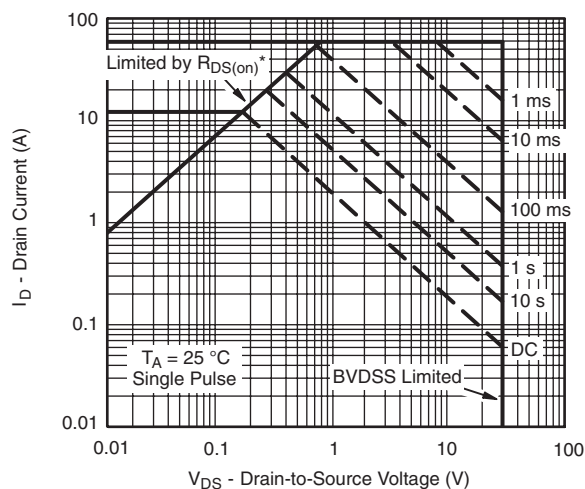
| SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted | | | | | | |
|--|-------------------------|---|-------|--------|-----------|------------------------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V_{DS} | $V_{GS} = 0\text{ V}$, $I_D = -250\text{ }\mu\text{A}$ | - 30 | | | V |
| V_{DS} Temperature Coefficient | $\Delta V_{DS}/T_J$ | $I_D = -250\text{ }\mu\text{A}$ | | - 32 | | mV/ $^{\circ}\text{C}$ |
| $V_{GS(th)}$ Temperature Coefficient | $\Delta V_{GS(th)}/T_J$ | | | 5.4 | | |
| Gate-Source Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$ | - 1.0 | | - 2.5 | V |
| Gate-Source Leakage | I_{GSS} | $V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$ | | | - 1 | μA |
| | | $V_{DS} = -30\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$ | | | - 5 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \geq -10\text{ V}$, $V_{GS} = -10\text{ V}$ | - 30 | | | A |
| Drain-Source On-State Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -10\text{ V}$, $I_D = -15\text{ A}$ | | 0.0058 | 0.007 | Ω |
| | | $V_{GS} = -4.5\text{ V}$, $I_D = -10\text{ A}$ | | 0.0085 | 0.0105 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -10\text{ V}$, $I_D = -15\text{ A}$ | | 45 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = -15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$ | | 5170 | | pF |
| Output Capacitance | C_{oss} | | | 930 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 890 | | |
| Total Gate Charge | Q_g | $V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -10\text{ A}$ | | 118 | 180 | nC |
| | | $V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -10\text{ A}$ | | 63 | 95 | |
| Gate-Source Charge | Q_{gs} | | | 14.3 | | |
| Gate-Drain Charge | Q_{gd} | | | 29.8 | | |
| Gate Resistance | R_g | $f = 1\text{ MHz}$ | 0.4 | 2.1 | 4.2 | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}$, $R_L = 1.5\text{ }\Omega$ $I_D \cong -10\text{ A}$, $V_{GEN} = -10\text{ V}$, $R_g = 1\text{ }\Omega$ | | 16 | 30 | ns |
| Rise Time | t_r | | | 15 | 30 | |
| Turn-Off DelayTime | $t_{d(off)}$ | | | 72 | 140 | |
| Fall Time | t_f | | | 17 | 30 | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = -15\text{ V}$, $R_L = 1.5\text{ }\Omega$ $I_D \cong -10\text{ A}$, $V_{GEN} = -4.5\text{ V}$, $R_g = 1\text{ }\Omega$ | | 73 | 140 | |
| Rise Time | t_r | | | 132 | 200 | |
| Turn-Off DelayTime | $t_{d(off)}$ | | | 65 | 100 | |
| Fall Time | t_f | | | 40 | 70 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continous Source-Drain Diode Current | I_S | $T_C = 25\text{ }^{\circ}\text{C}$ | | | - 30 | A |
| Pulse Diode Forward Current | I_{SM} | | | | - 60 | |
| Body Diode Voltage | V_{SD} | $I_S = -3\text{ A}$, $V_{GS} = 0\text{ V}$ | | - 0.72 | - 1.2 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = -10\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $T_J = 25\text{ }^{\circ}\text{C}$ | | 54 | 100 | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | | 50 | 100 | nC |
| Reverse Recovery Fall Time | t_a | | | 24 | | ns |
| Reverse Recovery Rise Time | t_b | | | 30 | | |

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

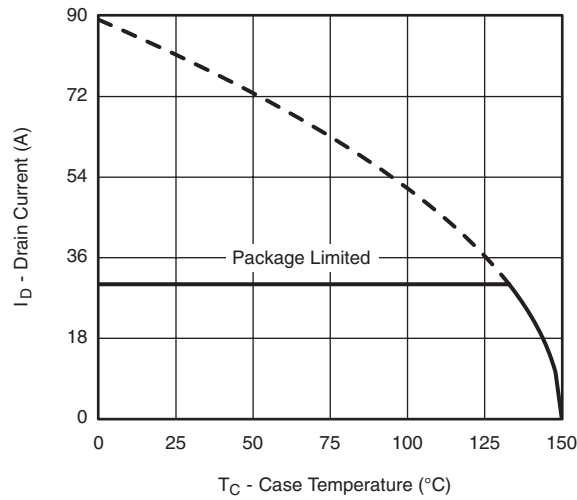
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Capacitance****Gate Charge****On-Resistance vs. Junction Temperature**

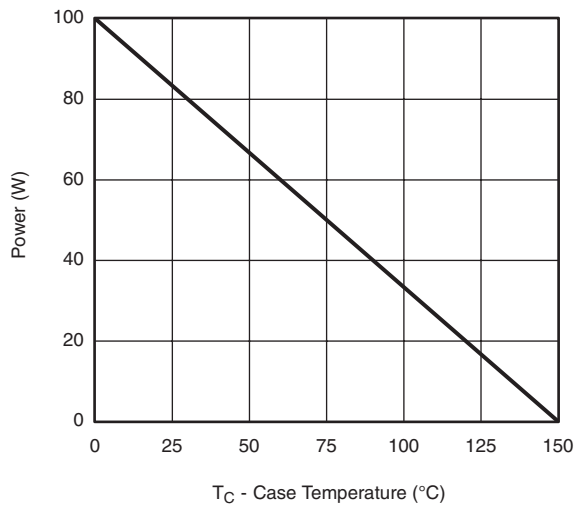
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Source-Drain Diode Forward Voltage****On-Resistance vs. Gate-to-Source Voltage****Threshold Voltage****Single Pulse Power, Junction-to-Ambient*** $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified**Safe Operating Area**



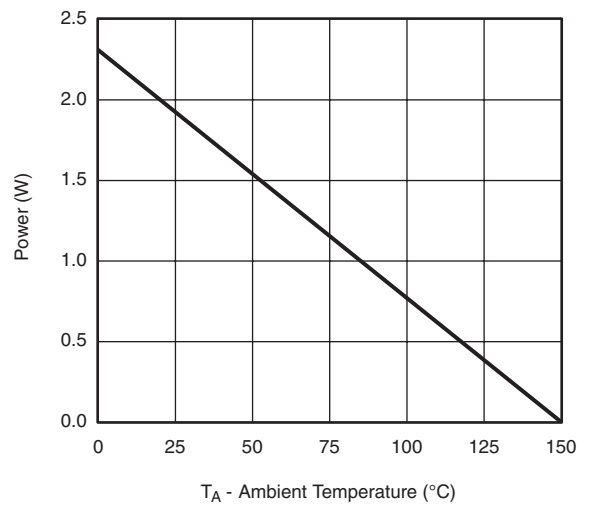
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*

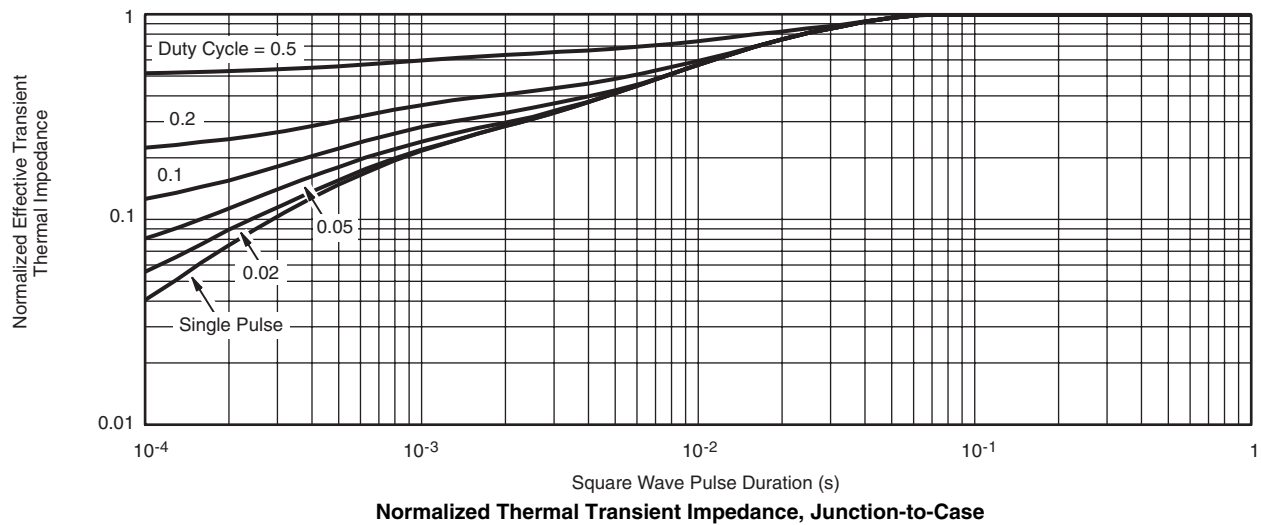
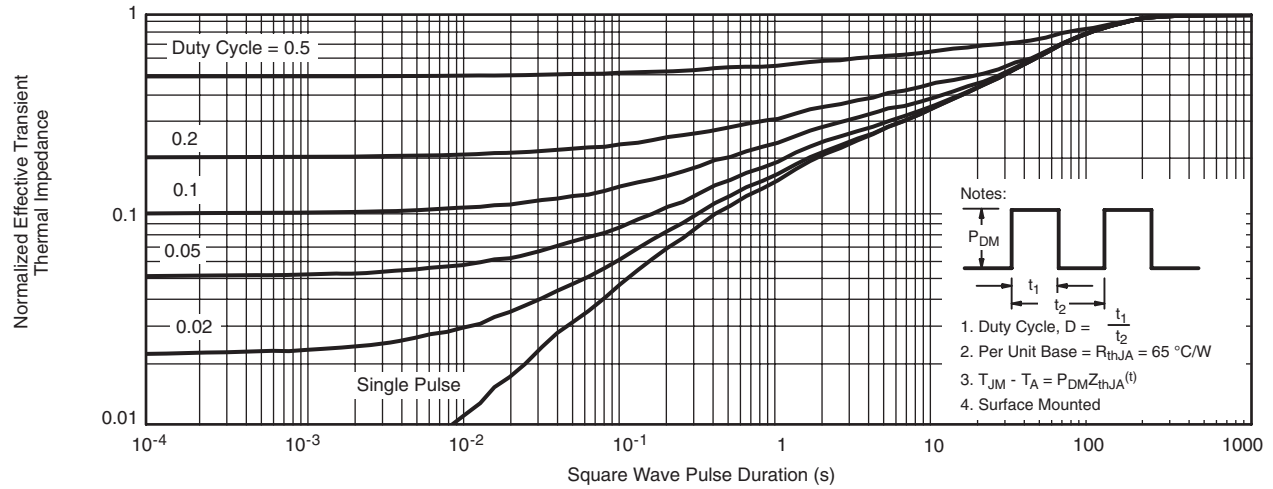


Power, Junction-to-Case



Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?68872>.

PowerPAK® SO-8, (Single/Dual)



Notes

1. Inch will govern.
2. Dimensions exclusive of mold gate burrs.
3. Dimensions exclusive of mold flash and cutting burrs.

| DIM. | MILLIMETERS | | | INCHES | | |
|---------------------------------|-------------|------|------|-------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.97 | 1.04 | 1.12 | 0.038 | 0.041 | 0.044 |
| A1 | | - | 0.05 | 0 | - | 0.002 |
| b | 0.33 | 0.41 | 0.51 | 0.013 | 0.016 | 0.020 |
| c | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 |
| D | 5.05 | 5.15 | 5.26 | 0.199 | 0.203 | 0.207 |
| D1 | 4.80 | 4.90 | 5.00 | 0.189 | 0.193 | 0.197 |
| D2 | 3.56 | 3.76 | 3.91 | 0.140 | 0.148 | 0.154 |
| D3 | 1.32 | 1.50 | 1.68 | 0.052 | 0.059 | 0.066 |
| D4 | 0.57 typ. | | | 0.0225 typ. | | |
| D5 | 3.98 typ. | | | 0.157 typ. | | |
| E | 6.05 | 6.15 | 6.25 | 0.238 | 0.242 | 0.246 |
| E1 | 5.79 | 5.89 | 5.99 | 0.228 | 0.232 | 0.236 |
| E2 (for AL product) | 3.30 | 3.48 | 3.66 | 0.130 | 0.137 | 0.144 |
| E2 (for other product) | 3.48 | 3.66 | 3.84 | 0.137 | 0.144 | 0.151 |
| E3 | 3.68 | 3.78 | 3.91 | 0.145 | 0.149 | 0.154 |
| E4 (for AL product) | 0.58 typ. | | | 0.023 typ. | | |
| E4 (for other product) | 0.75 typ. | | | 0.030 typ. | | |
| e | 1.27 BSC | | | 0.050 BSC | | |
| K (for AL product) | 1.45 typ. | | | 0.057 typ. | | |
| K (for other product) | 1.27 typ. | | | 0.050 typ. | | |
| K1 | 0.56 | - | - | 0.022 | - | - |
| H | 0.51 | 0.61 | 0.71 | 0.020 | 0.024 | 0.028 |
| L | 0.51 | 0.61 | 0.71 | 0.020 | 0.024 | 0.028 |
| L1 | 0.06 | 0.13 | 0.20 | 0.002 | 0.005 | 0.008 |
| θ | 0° | - | 12° | 0° | - | 12° |
| W | 0.15 | 0.25 | 0.36 | 0.006 | 0.010 | 0.014 |
| M | 0.125 typ. | | | 0.005 typ. | | |
| ECN: C13-0702-Rev. K, 20-May-13 | | | | | | |
| DWG: 5881 | | | | | | |

RECOMMENDED MINIMUM PADS FOR PowerPAK® SO-8 Single



Recommended Minimum Pads
Dimensions in Inches/(mm)

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